

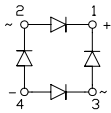
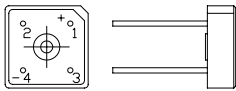
DIODE Type:**PB10S1,2,4,6**

OUTLINE DRAWING

SINGLE – PHASE SILICON BRIDGE RECTIFIER

FEATURES

- * Surge Overload Rating : 150 Amperes Peak
- * Low Forward Voltage Drop
- * Mounting Position : Any



Maximum Ratings

Approx Net Weight:8.5g

Rating	Symbol	PB10S1	PB10S2	PB10S4	PB10S6	Unit
Repetitive Peak Reverse Voltage	V _{RRM}	100	200	400	600	V
Non-repetitive Peak Reverse Voltage	V _{RSM}	120	240	480	680	V
Average Rectified Output Current	I _O	10	Tc=102°C, With 200x200x1.5mm,Al-Fin Ta=40°C, Without Fin			A
		3.7				
Surge Forward Current Per 1 Arm	I _{FSM}	150	50 Hz Half Sine Wave,1cycle Non-repetitive			A
Operating JunctionTemperature Range	T _{jw}	- 40 to + 150				°C
Storage Temperature Range	T _{stg}	- 40 to + 150				°C
Insuration Withstand Voltage	V _{iso}	1500	Terminal to Base, AC 1min.			V
Mounting torque	F _w	0.5	Recommended value			N•m

Electrical • Thermal Characteristics

Characteristics	Symbol	Conditions	Min.	Typ.	Max.	Unit
Peak Reverse Current Per 1 Arm	I _{RM}	Tj= 25°C, V _{RM} = V _{RRM}	-	-	5	μA
Peak Forward Voltage Per 1 Arm	V _{FM}	Tj= 25°C, I _{FM} = 5A	-	-	1.0	V
Thermal Resistance	Rth(j-c)	Junction to Case(total)	-	-	3.5	°C/W

PB10S1,2,4,6 OUTLINE DRAWING (Dimensions in mm)

